

ULTRA LOW MAGNETIC MOMENT PIN DIODE FOR MRI APPLICATIONS

RoHS COMPLAINT

RoHS

www.MICROSEMI.com

e4

DESCRIPTION

The UMX5601[™] PIN diode series was designed to provide ultra low magnetic PIN diodes for in bore surface coil applications associated with higher field strength (3T and greater) MR scanners. These PIN diodes produce the minimum artifacts (magnetic field distortions) available in the industry, today. The diodes have been tested in magnetic fields of ±7 Tesla.

The UMX5601 PIN diodes have a magnetic moment at 7 T of 4E-8 (J/T). The diodes are offered in a surface mount package. The SM package utilizes a round end cap to mark the anode. The cathode is square. The fully passivated PIN diode chip is full face metallurgically bonded to shortened high conductive pins for lower thermal and electrical resistances. The PIN diodes feature low forward bias resistance and high zero bias impedance. The UMX5601 PIN diodes are characterized at 64, 128, and 300 MHz. The UMX5601SM meets RoHS requirements per EU Directive 2002/95/EC.

IMPORTANT: Forthemost current data, consult MICROSEMI's website: www.microsemi.com

	OLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED) ting Symbol Value Unit						
Rating	Symbol	Value	Unit				
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	100 100 100	V				
RMS Reverse Voltage	V _{R (RMS)}	75	V				
Storage Temperature	T stg	-65 to +175	°C				
Operating Temperature Non-Repetitive Peak	Т ор	-65 to +150	°C				

THERMAL CHARACTERISTICS						
(UNLESS OTHERWISE SPECIFIED)						
Thermal Resistance	Symbol	Value	Unit			
UMX5601SM	θ	2	°C/Watt			



KEY FEATURES

- Ultra low magnetic construction
- SOGO passivated chip
- Thermally matched configuration
- RoHS compliant ¹
- Low capacitance at 0 V bias
- Low conductance at 0 V bias
- Metallurgical bond
- Fused-in-glass construction
- Non cavity design
- Available in surface mount package.
- Compatible with automatic insertion equipment

1- These devices are supplied with Silver terminations. Other terminal finishes may be available on request. Consult factory for details.

APPLICATIONS/BENEFITS

- High B Field (3T+) in bore APPLICATIONS:
- Active or semi-active (not passive)
- MR blocking circuits
- MR detuning circuits
- MR disable circuits
- MR receiver protector circuits



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ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified)									
Parameter	Symbol	Conditions	Min	Тур.	Max	Units			
Forward Voltage (Note 1)	VF	I _F = 100 mA		0.75	1.0	V			
Reverse Break Down Voltage	V _{BR}	I _R = 10 uA	100			V			
Reverse Current	I _R	V _R = 100 V			10	uA			
Inductance	Ls			900		pН			
Magnetic moment	m	@ 7T @ 1T		4E-8 1E-7		J/T J/T			
Mass Susceptibility	χρ	@ 7T @ 1T		-3.3E-11 6.5E-10		m ³ /kg m ³ /kg			
Volume Susceptibility	χ	>1T to 7T <1 T		-3.1E-7 5.9E-6		SI SI			
Capacitance	Ст	$V_R = 0 V, F = 1 MH_Z$ $V_R = 50 V, F = 1 MH_Z$		9 2.6	10 3.0	pF			
Parallel Resistance	Rp	$V_R = 0 V, F = 64 MHz$ $V_R = 30 V, F = 64 MHz$	5 100	9 250		kOhms			
Series Resistance	Rs	If = 100 mA F = 64 MHz		0.3	0.5	Ohms			
Lifetime	τ	If = 10 mA	5	10		us			



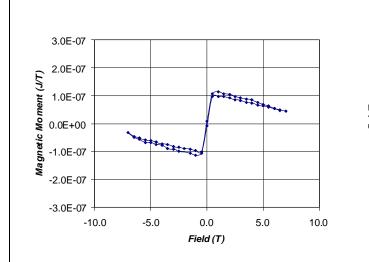
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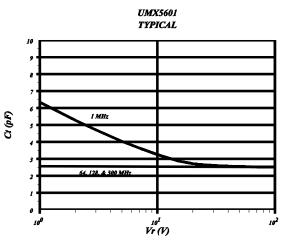
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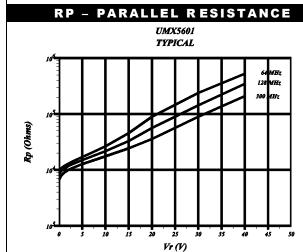
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MAGNETIC MOMENT VS FIELD

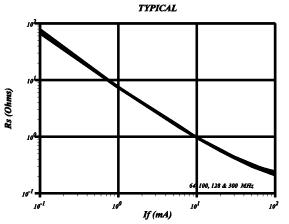
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GRAPHS

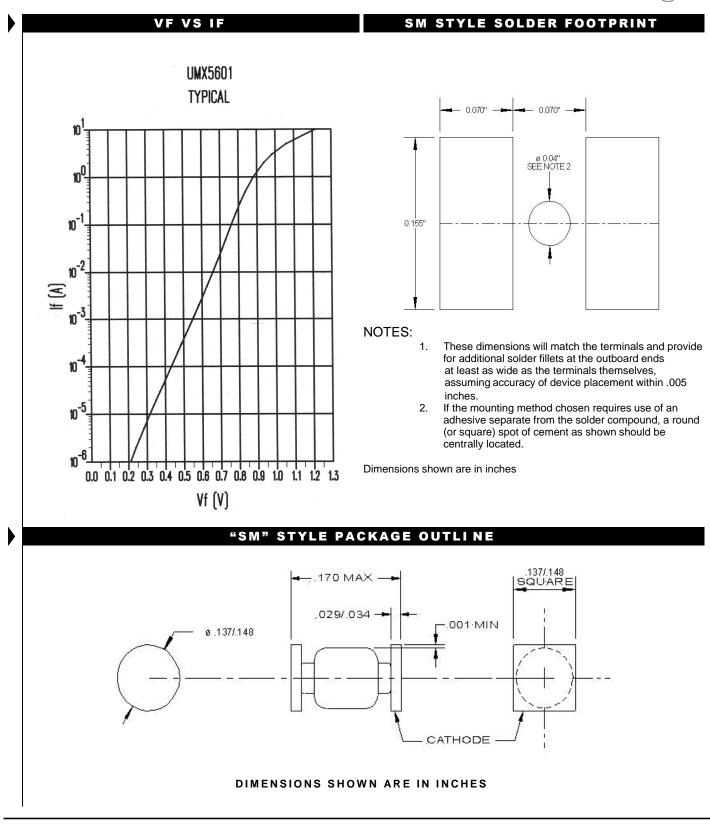
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